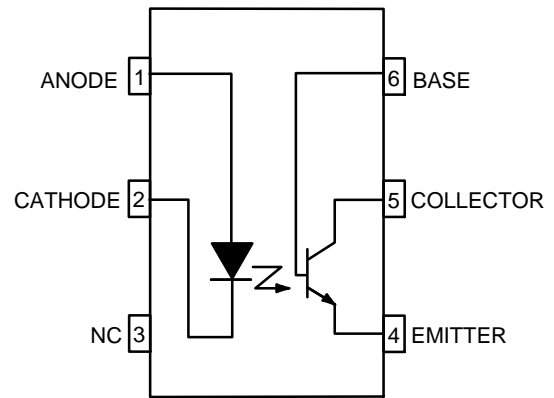
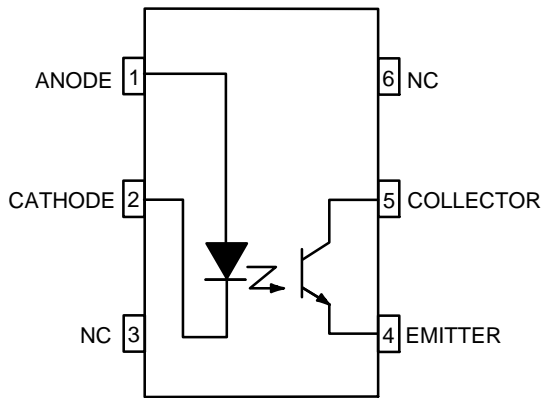


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Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage		< 150 V _{RMS}	I-IV
		< 300 V _{RMS}	I-IV
Climatic Classification		55/100/21	
Pollution Degree (DIN VDE 0110/1.89)		2	
Comparative Tracking Index		175	

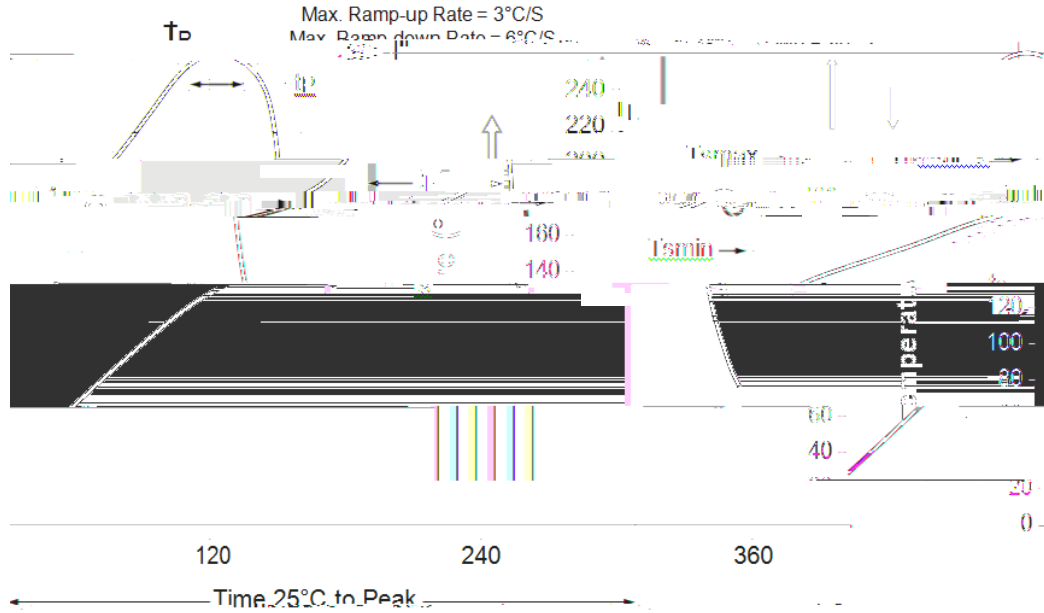
V _{PR}	Input-to-Output Test Voltage, Method A, V _{IORM} x 1.6 = V _{PR} , Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC	1360	V _{peak}
	Input-to-Output Test Voltage, Method B, V _{IORM} x 1.875 = V _{PR} , ito-		

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T_{STG}	Storage Temperature	-40 to +125	C
T_A	Ambient Operating Temperature	-40 to +100	C
T_J	Junction Temperature	-40 to +125	C
T_{SOL}	Lead Solder Temperature	260 for 10 seconds	C
P_D	Total Device Power Dissipation @ 25 C (LED plus detector) Derate Linearly From 25 C	270	mW
		2.94	mW/ C

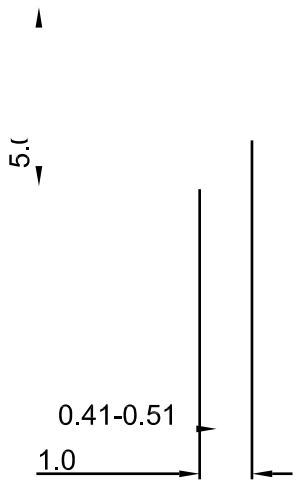
I_F	Continuous Forward Current	60	mA
V_R	Reverse Voltage	6	V
$I_F (pk)$	Forward Current – Peak (1 μ s pulse, 300 pps)	1.5	A
P_D	LED Power Dissipation 25 C Ambient Derate Linearly From 25 C	120	mW
		1.41	mW/ C

I_C	Continuous Collector Current	50	mA
V_{CEO}	Collector–Emitter Voltage	70	V



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Temperature Min. (T _{min})		150°C
Temperature Max. (T _{max})		200°C
Time (t _S) from (T _{min} to T _{max})		60–120 seconds
Ramp – up Rate (t to t _p)		3°C/second max.
Liquidous Temperature (T _L)		217°C
Time (t _L) Maintained Above (T _L)		60–150 seconds
Peak Body Package Temperature		260°C +0°C / –5°C
Time (t _p) within 5°C of 260°C		30 seconds
Ramp – down Rate (T _p to T _L)		6°C / second max.
Time 25°C to Peak Temperature		8 minutes max.

		†
CNY171M	DIP 6–Pin	Tube (50 Units)
CNY171SM	SMT 6–Pin (Lead Bend)	Tube (50 Units)
CNY171SR2M	SMT 6–Pin (Lead Bend)	Tape and Reel (1000 Units)
CNY171TM	DIP 6–Pin, 0.4" Lead Spacing	Tube (50 Units)
CNY171VM	DIP 6–Pin, DIN EN/IEC60747–5–5 Option	Tube (50 Units)
CNY171SVM		

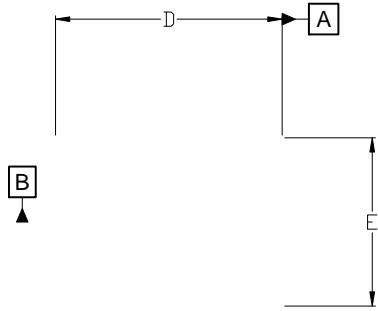


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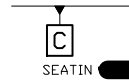


PDIP6 8.51x6.35, 2.54P
CASE 646BY
ISSUE A

DATE 15 JUL 2019



TOP VIEW



ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIM ■

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